

PNP General Purpose Transistor

SSTA56 / MMSTA56 / MPSA56

●Features

- 1) $BV_{CE0} < -80V$ ($I_c = -1mA$)
- 2) Complements the SSTA06 / MMSTA06 / MPSA06.

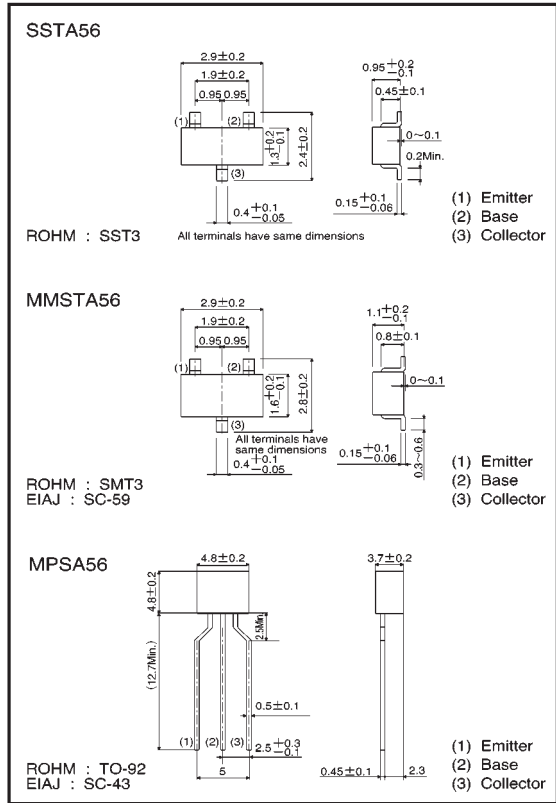
●Package, marking and packaging specifications

Part No.	SSTA56	MMSTA56	MPSA56
Packaging type	SST3	SMT3	TO-92
Marking	R2G	R2G	—
Code	T116	T146	T93
Basic ordering unit (pieces)	3000	3000	3000

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	-80	V
Collector-emitter voltage	V_{CE0}	-80	V
Emitter-base voltage	V_{EB0}	-4	V
Collector current	I_c	-0.5	A
Collector power dissipation	P_c	0.2 0.625	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55~+150	$^\circ C$

●External dimensions (Units : mm)



●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	-4	—	—	V	$I_c = -100 \mu A$
Collector-emitter breakdown voltage	BV_{CE0}	-80	—	—	V	$I_c = -1mA$
Collector cutoff current	I_{cbo}	—	—	-0.1	μA	$V_{ce} = -80V$
	I_{cec}	—	—	-1		$V_{ce} = -60V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.25	V	$I_c/I_e = -100mA/-10mA$
Base-emitter saturation voltage	$V_{BE(on)}$	—	—	-1.2	V	$V_{ce}/I_e = -1V/-100mA$
DC current transfer ratio	h_{FE}	100	—	—	—	$V_{ce} = -1V, I_c = -10mA$
		100	—	—	—	$V_{ce} = -1V, I_c = -100mA$
Transition frequency	f_T	50	—	—	MHz	$V_{ce} = -1V, I_e = 100mA, f = 100MHz$

● Electrical characteristic curves

